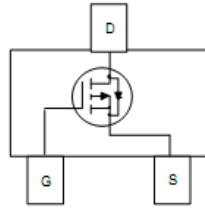
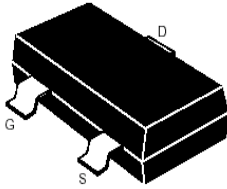


SOT-23

Features

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance

MAXIMUM RANTINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 12	V
Drain Current (continuous)	I_D	-4.2	A
Drain Current (pulsed)	I_{DM}	-18	A
Total Device Dissipation $T_A=25^\circ C$	P_D	1400	mW
Junction	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55to+150	$^\circ C$

Electrical Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage ($I_D = -250\mu A, V_{GS}=0V$)	BV_{DSS}	-30	—	—	V
Gate Threshold Voltage ($I_D = -250\mu A, V_{GS}= V_{DS}$)	$V_{GS(th)}$	-0.6	—	-2	V
Diode Forward Voltage Drop ($I_S = -1 A, V_{GS}=0V$)	V_{SD}	—	—	-1	V
Zero Gate Voltage Drain Current ($V_{GS}=0V, V_{DS}= -24V$) ($V_{GS}=0V, V_{DS}= -24V, T_A=55^\circ C$)	I_{DSS}	—	—	-1 -5	μA
Gate Body Leakage ($V_{GS}=\pm 12V, V_{DS}=0V$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance ($I_D= -4.1A, V_{GS}= -10V$)	$R_{DS(ON)}$	—	42	50	$m\Omega$
Static Drain-Source On-State Resistance ($I_D= -2A, V_{GS}= -4.5V$)	$R_{DS(ON)}$	—	53	60	$m\Omega$
Static Drain-Source On-State Resistance ($I_D= -1A, V_{GS}= -2.5V$)	$R_{DS(ON)}$	—	80	85	$m\Omega$
Input Capacitance ($V_{GS}=0V, V_{DS}= -15V, f=1MHz$)	C_{ISS}	—	954	—	pF
Output Capacitance ($V_{GS}=0V, V_{DS}= -15V, f=1MHz$)	C_{OSS}	—	115	—	pF
Turn-ON Time ($V_{DS}= -15V, V_{GS}=-10 V, R_{GEN}=6\Omega$)	$t_{(on)}$	—	6	—	ns
Turn-OFF Time ($V_{DS}= -15V, V_{GS}=-10 V, R_{GEN}=6\Omega$)	$t_{(off)}$	—	38	—	ns

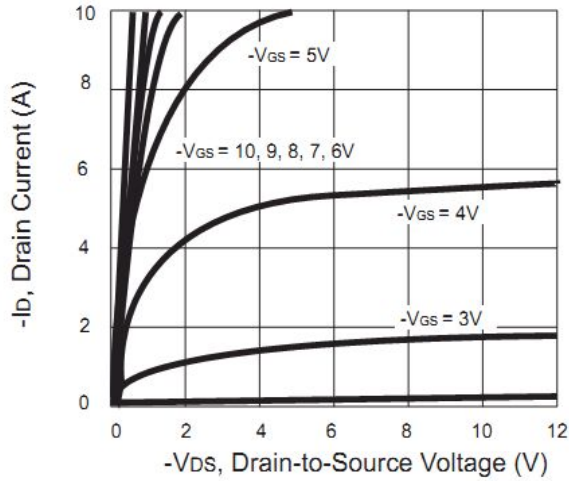


Fig 1: Output Characteristics

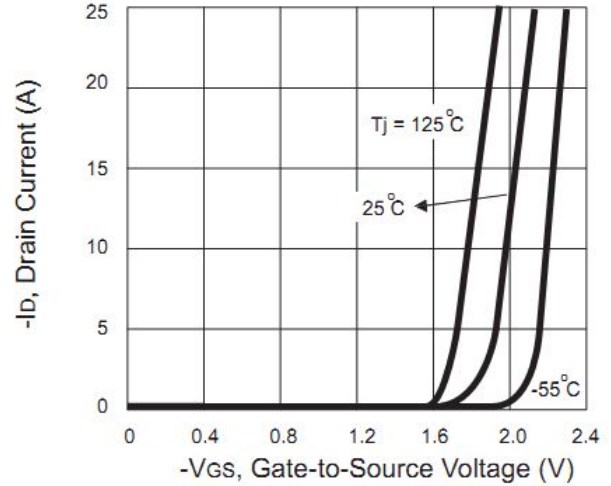


Figure 2: Transfer Characteristics

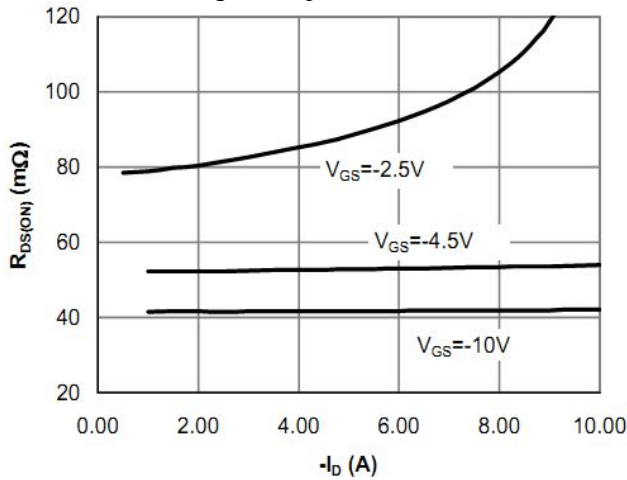


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

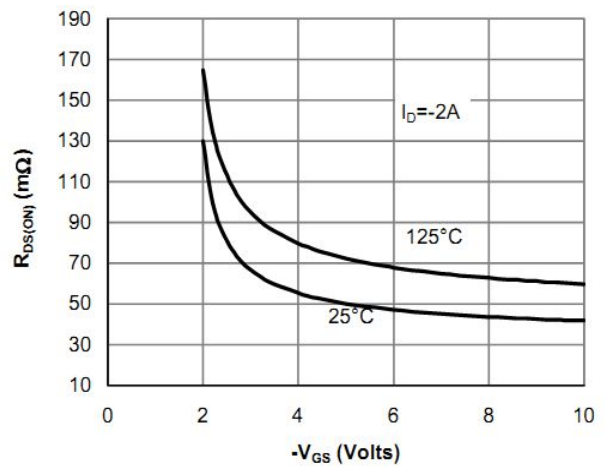


Figure 4: On-Resistance vs. Gate-Source Voltage

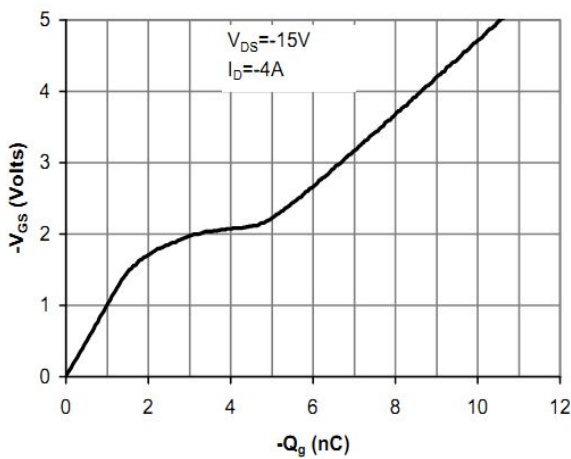


Figure 5: Gate-Charge Characteristics

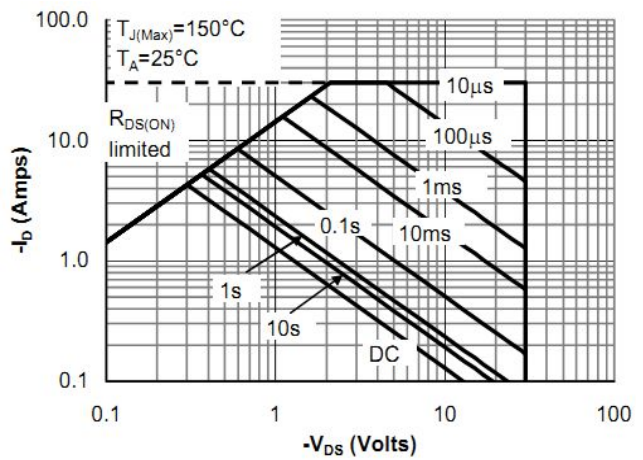
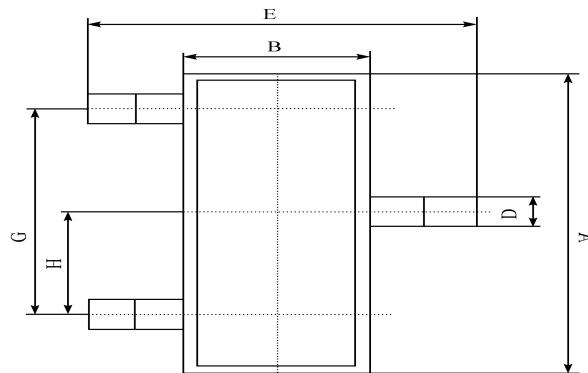


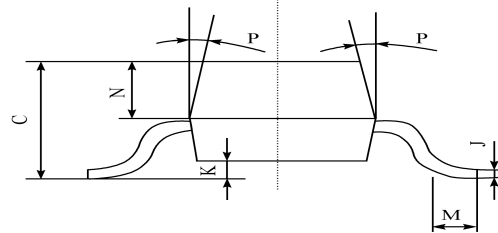
Figure 6: Safe Operating Area

SOT-23 PACKAGE OUTLINE Plastic surface mounted package



SOT-23	
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00 - 0.10
M	≥ 0.2
N	0.60 ± 0.10
P	7 ± 2°

(UNIT): mm



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